• <u> </u>			<u> </u>	
L Number		Search Text	DB	Time stamp
1	10		USPAT;	2003/06/27 10:11
		adj transistor) and (ion adj implant) and	US-PGPUB; EPO; JPO;	
		(angl\$3 with dopant)	DERWENT	
	2124	(field adj effect adj transistor) and (ion	USPAT;	2003/06/27 08:39
-	2124	adj implant)	US-PGPUB;	2003/00/2/ 00:33
		adj impiant/	EPO; JPO;	
		•	DERWENT	
_	6	438/525.ccls. and (field adj effect adj	USPAT;	2003/06/27 10:10
		transistor) and (ion adj implant) and	US-PGPUB;	
1		(angl\$3 with dopant)	EPO; JPO;	
t l			DERWENT	
l –	85	(field adj effect adj transistor) and (ion	USPAT;	2003/06/20 19:01
		adj implant) and (angl\$3 with dopant)	US-PGPUB;	
			EPO; JPO;	
	_		DERWENT	2002/06/20 10:56
-	34	(field adj effect adj transistor) and (ion	USPAT;	2003/06/20 18:56
		adj implant) and (angl\$3 with dopant) and	US-PGPUB; EPO; JPO;	
		(gate adj electrode)	DERWENT	
	34	 (field adj effect adj transistor) and (ion	USPAT;	2003/06/21 13:44
-	34	(field adj effect adj transistor, and (for adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain)	DERWENT	
_	5	l '	USPAT;	2003/06/20 18:59
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (lithography)	DERWENT	
-	0	(field adj effect adj transistor) and (ion	USPAT;	2003/06/20 19:00
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (pocket adj region)	DERWENT	2003/06/20 19:02
-	4	438/197.ccls. and (field adj effect adj	USPAT; US-PGPUB;	2003/06/20 19:02
		transistor) and (ion adj implant) and	EPO; JPO;	
		(angl\$3 with dopant)	DERWENT	
	27	(field adj effect adj transistor) and (ion	USPAT;	2003/06/20 19:04
	- '	adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (mask)	DERWENT	
_	0	(field adj effect adj transistor) and (ion	USPAT;	2003/06/20 19:05
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (mask) and (conductive adj	DERWENT	
		region)	HCDAM.	2003/06/20 19:05
-	5	(field adj effect adj transistor) and (ion	USPAT; US-PGPUB;	2003/00/20 19:05
		adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (mask) and (conductive adj	DERWENT	
		layer)		
l _	6		USPAT;	2003/06/20 19:06
1	I	adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
1	1	(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (mask) and (conduct\$3 adj	DERWENT	
		layer)		
-	18		USPAT;	2003/06/21 15:51
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
	1	(drain) and (mask with electrode)	DERWENT USPAT;	2003/06/21 16:05
1 -	12	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and	US-PGPUB;	2003,00,21 10.03
		(gate adj electrode) and (source) and	EPO; JPO;	
	1	(drain) and (mask with spacer)	DERWENT	
_	1	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 15:57
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
[(gate adj electrode) and (source) and	EPO; JPO;	
1	l .	(drain) and (mask with dielectric adj	DERWENT	1
1	i	(

-	0	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 16:07
		adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and	US-PGPUB; EPO; JPO;	
		(drain) and (taper with electrode)	DERWENT	
-	0	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 16:11
		adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and	US-PGPUB; EPO; JPO;	
		(drain) and (taper\$2 with electrode)	DERWENT	
-	5	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 16:12
		adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and	US-PGPUB; EPO; JPO;	
		(drain) and (reduced with electrode)	DERWENT	
-	0	EP-1263027\$.did.	USPAT;	2003/06/27 08:41
			US-PGPUB; EPO; JPO;	
			DERWENT	
-	2	EP-1263027-\$.did.	USPAT;	2003/06/27 09:04
			US-PGPUB; EPO; JPO;	
			DERWENT	
_	12213048	US 5731239.pn.	USPAT;	2003/06/27 08:54
			US-PGPUB; EPO; JPO;	
			DERWENT	
_	2	5731239.pn.	USPAT;	2003/06/27 08:57
			US-PGPUB; EPO; JPO;	
	· ·		DERWENT	
-	4	512063.pn.	USPAT;	2003/06/27 08:58
			US-PGPUB; EPO; JPO;	
			DERWENT	
_	2	5120637.pn.	USPAT;	2003/06/27 08:58
			US-PGPUB; EPO; JPO;	
			DERWENT	
-	2	5120673.pn.	USPAT;	2003/06/27 09:10
			US-PGPUB; EPO; JPO;	
			DERWENT	
-	0	JP-88317951-\$.did.	USPAT; US-PGPUB;	2003/06/27 09:23
			EPO; JPO;	
			DERWENT	
-	0	JP-2162738-\$.did.	USPAT; US-PGPUB;	2003/06/27 09:06
			EPO; JPO;	
			DERWENT	0002/06/07 00 07
-	0	JP-2162738 A-\$.did.	USPAT; US-PGPUB;	2003/06/27 09:07
			EPO; JPO;	
		5001355	DERWENT	2003/06/27 00-12
-	2	5021355.pn.	USPAT; US-PGPUB;	2003/06/27 09:13
			EPO; JPO;	
		C501122	DERWENT	2003/06/27 09:15
-	2	6501133.pn.	USPAT; US-PGPUB;	2003/00/2/ 09:15
			EPO; JPO;	
	_	2020050621 22	DERWENT USPAT;	2003/06/27 09:25
-	0	2020050621.pn.	US-PGPUB;	2003/00/27 09.25
			EPO; JPO;	
	0	2000648044.pn.	DERWENT USPAT;	2003/06/27 09:17
		2000046044.pm.	US-PGPUB;	2003,00,27 03.17
			EPO; JPO;	
	2	20020050621.pn.	DERWENT USPAT;	2003/06/27 09:18
		2002000021.pm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT	

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Γ-	2	5731239.pn.	USPAT;	2003/06/27 09:19
		•	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT	
-	2	5120673.pn.	USPAT;	2003/06/27 09:19
		•	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT	
 	1	JP-56048174-\$.did.	USPAT;	2003/06/27 09:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
_	2	5021355.pn.	USPAT;	2003/06/27 09:25
		-	US-PGPUB;	
			EPO; JPO;	1
			DERWENT	1